

FEATURES

High voltage transistor

MMBTA92 (PNP)
MARKING: 2D
MAXIMUM RATINGS (TA=25 °C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-300	V
Collector-Emitter Voltage	V _{CEO}	-300	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current -Continuous	I _C	-500	mA
Collector Power Dissipation	P _C	0.3	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C
Thermal Resistance, junction to Ambient	R _{JA}	410	°C/mW


ELECTRICAL CHARACTERISTICS (Tamb=25 °C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V _{CBO}	I _C = -100μA, I _E =0	-300		V
Collector-emitter breakdown voltage	V _{CEO}	I _C = -1mA, I _B =0	-300		V
Emitter-base breakdown voltage	V _{EBO}	I _E = -100μA, I _C =0	-5		V
Collector cut-off current	I _{CB}	V _{CB} =-200V, I _E =0		-0.25	μA
Emitter cut-off current	I _{EB}	V _{EB} = -5V, I _C =0		-0.1	μA
DC current gain	hFE(1)	V _{CE} = -10V, I _C = -1mA	60		
	hFE(2)	V _{CE} = -10V, I _C =-10mA	100	200	
	hFE(3)	V _{CE} = -10V, I _C =-30mA	60		
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-20mA, I _B = -2mA		-0.2	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = -20mA, I _B = -2mA		-0.9	V
Transition frequency	f _T	V _{CE} =-20V, I _C = -10mA f=30MHz	50		MHz

MMBTA92 Typical Characteristics

